Revision. 3

MOS FET

FK8V03040L

Panasonic

FK8V03040L

Silicon N-channel MOSFET

For lithium-ion secondary battery protection circuit For DC-DC Converter

■ Features

- Low drain-source On-state Resistance RDS(on) typ = 11 m Ω (VGS = 4.5 V)
- High-speed switching : Qg = 7.2 nC
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: 3D

Established: 2011-04-06

: 2013-07-31

Revised

■ Packaging

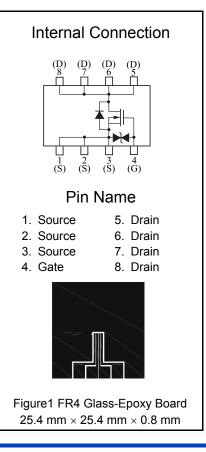
Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

Unit: mm 0.16 (0.81)0.65 5. Drain 1. Source 2. Source 6. Drain 3. Source 7. Drain 8. Drain 4. Gate WMini8-F1 Panasonic JEITA SC-115 Code

Parameter	Symbol	Rating	Unit	
Drain-source Voltage	VDS	33	V	
Gate-source Voltage	VGS	±20	V	
Drain Current (Steady State) *1	ID	10		
Drain Current (t = 10 s) *1	טו	12		
Drain Current (Pulsed) *1,*2	IDp	40	Α	
Source Current (Pulsed)	ISp	10		
(Body Diode) *1,*2	(BD)	10		
Total Power Dissipation (Steady State) *1	PD	1	W	
Total Power Dissipation (t = 10 s) *1	טו	1.5	V V	
Channel Temperature	Tch	150	°C	
Operating Ambient Temperature	Topr	-40 to +85	°C	
Storage Temperature Range	Tstg	-55 to +150	°C	
·				

Note) *1 Device mounted on a glass-epoxy board (See Figure 1)

*2 Pulse test: Ensure that the channel temperature does not exceed 150°C.



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FK8V03040L

■ Electrical Characteristics Ta = 25°C ± 3°C

Static Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	33			V
Zero Gate Voltage Drain Current	IDSS	VDS = 33 V, VGS = 0 V			10	μΑ
Gate-source Leakage Current	IGSS	VGS = $\pm 16 \text{ V}$, VDS = 0 V			±10	μΑ
Gate-source Threshold Voltage	Vth	ID = 1.12 mA, VDS = 10 V	1		2.5	V
		ID = 5A, VGS = 10 V		7	10	mΩ
	RDS(on)2	ID = 5A, VGS = 4.5 V		11	19	

Dynamic Characteristics

- ,					
Input Capacitance	Ciss	VDS = 10 V VCS = 0 V	750		
Output Capacitance	Coss	VDS = 10 V, VGS = 0 V f = 1 MHz	170	р	ρF
Reverse Transfer Capacitance	Crss	1 - 1 1011 12	100		
Turn-on Delay Time *2	td(on)	VDD = 15 V, VGS = 0 to 10 V	9		
Rise Time *2	tr	ID = 5 A	6		20
Turn-off Delay Time *2	td(off)	VDD = 15 V, VGS = 10 to 0 V	46		ns
Fall Time *2	tf	ID = 5 A	18		
Total Gate Charge	Qg	VDD = 15 V, VGS = 0 to 4.5 V,	7.2		
Gate-source Charge	Qgs	ID = 10 A	2.3	n	ıC
Gate-drain Charge	Qgd	7 10 - 10 /	3.3	_	

Body Diode Characteristic					
Diode Forward Voltage *1	VSD	IS = 5 A, VGS = 0 V	8.0	1.2	V

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

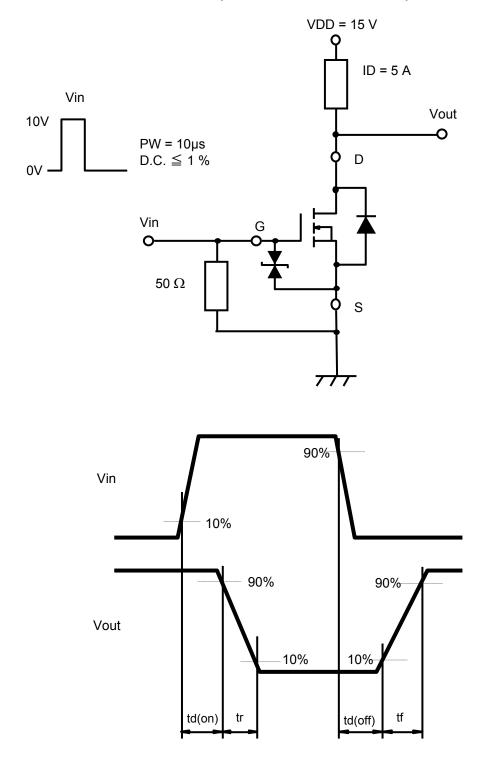
^{2. *1} Pulse test: Ensure that the channel temperature does not exceed 150°C.

^{*2} Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

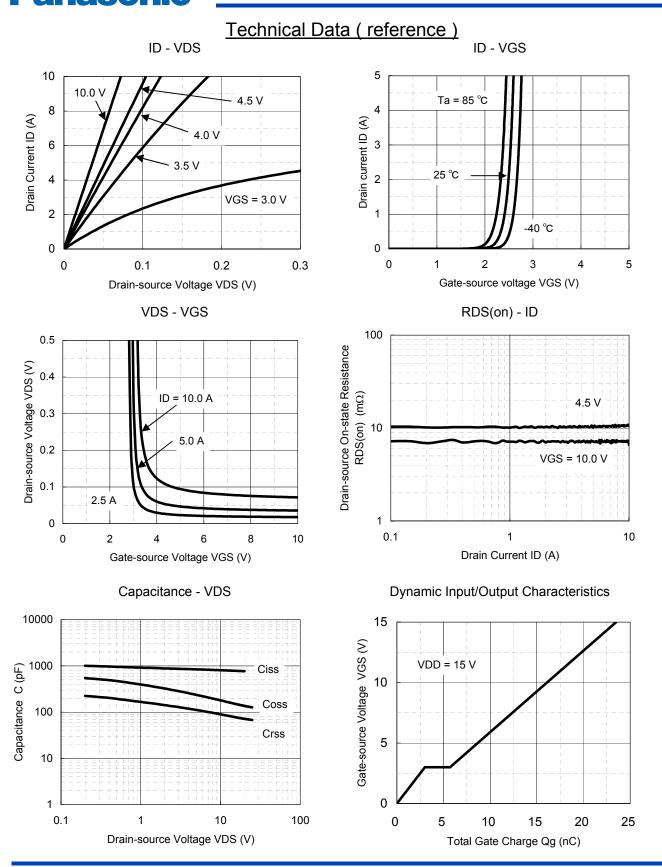
FK8V03040L

MOS FET

*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time



MOS FET FK8V03040L



Page 4 of 6

2.5

2

1.5

1

0.5

0

-50

Gate-source Threshold Voltage (V)

MOS FET FK8V03040L

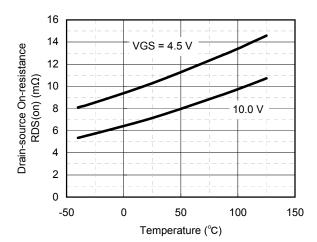
Technical Data (reference)

150



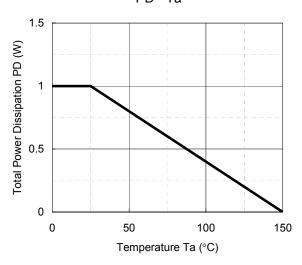


RDS(on) - Ta

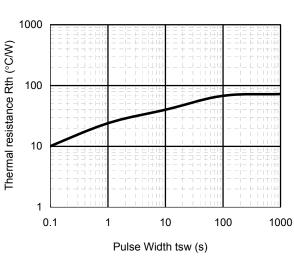


Temperature (°C)
PD - Ta

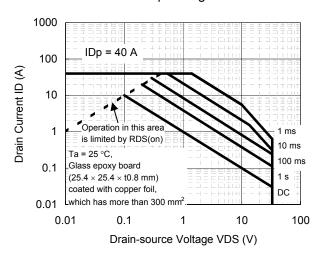
50



Rth - tsw



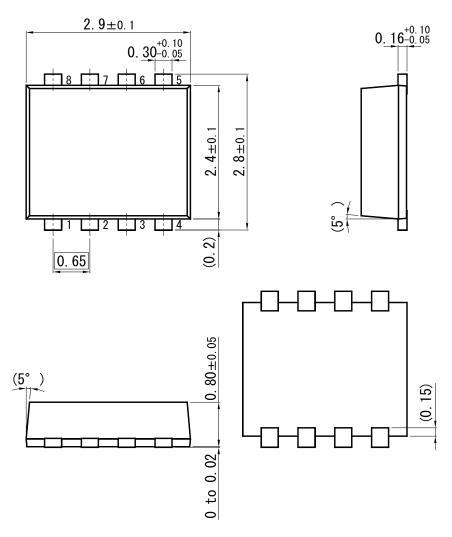
Safe Operating Area



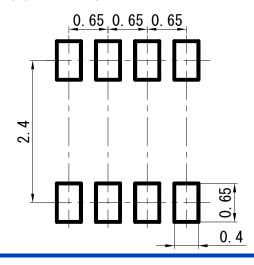
Page 5 of 6

MOS FET FK8V03040L

WMini8-F1 Unit: mm



■ Land Pattern (Reference) (Unit: mm)



Page 6 of 6

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